

SANYO Semiconductors DATA SHEET

2SC3807 — High-hFE, Low Frequency General-Purpose Amplifier Applications

Applications

· Low-frequency general-purpose amplifiers, drivers.

Features

- Large current capacity (IC=2A).
- · Adoption of MBIT process.
- High DC current gain (hFE=800 to 3200).
- · Low collector-to-emitter saturation voltage (VCE(sat)≤0.5V).
- High VEBO (VEBO≥15V).

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		30	٧
Collector-to-Emitter Voltage	VCEO		25	V
Emitter-to-Base Voltage	VEBO		15	V
Collector Current	IC		2	Α
Collector Current (Pulse)	ICP		4	Α
Collector Dissipation	PC		1.2	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

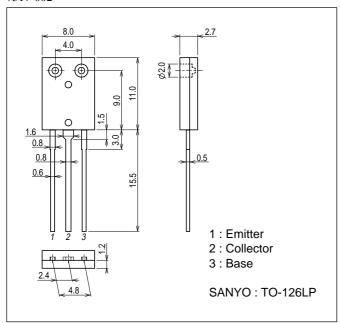
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Electrical Characteristics at Ta=25°C

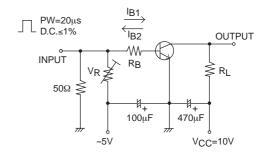
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ІСВО	VCB=20V, IE=0A			0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =10V, I _C =0A			0.1	μΑ
DC Current Gain	hFE1	VCE=5V, IC=500mA	800	1500	3200	
	hFE2	VCE=5V, IC=1A	600			
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =50mA		260		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		27		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =1A, I _B =20mA		0.15	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =1A, I _B =20mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	30			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	25			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	15			V
Turn-ON Time	ton	See specified Test Circuit.		0.14		μS
Storage Time	t _{stg}	See specified Test Circuit.		1.35		μS
Fall Time	tf	See specified Test Circuit.		0.1		μS

Package Dimensions

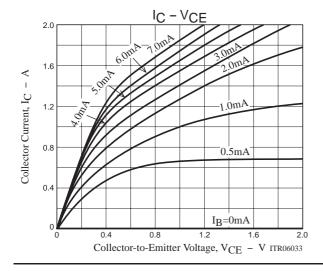
unit : mm (typ) 7517-002

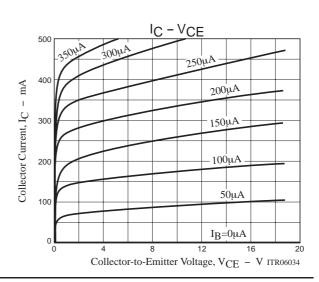


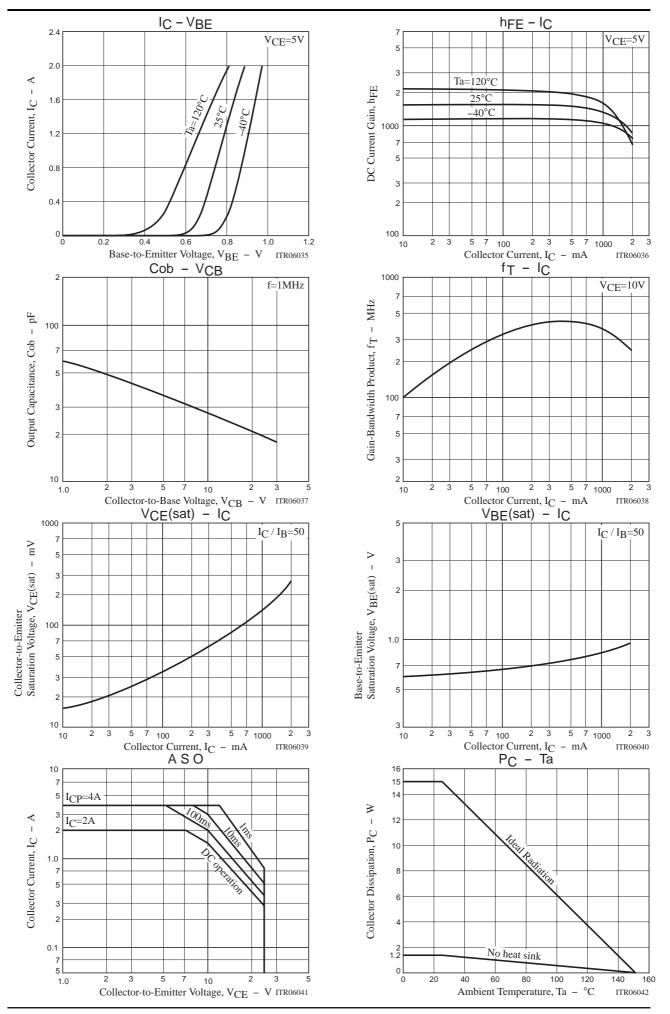
Switching Time Test Circuit



 $7I_{B1} = -7I_{B2} = I_{C} = 700 \text{mA}$







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